

### **Vishay Siliconix**

## N-Channel 60-V (D-S) MOSFET

PRODUCT	SUMMARY			
Part Number	V <sub>(BR)DSS</sub> Min (V)	r <sub>DS(on)</sub> Max (Ω)	V <sub>GS(th)</sub> (V)	I <sub>D</sub> (A)
2N7000		5 @ V <sub>GS</sub> = 10 V	0.8 to 3	0.2
2N7002		7.5 @ V <sub>GS</sub> = 10 V	1 to 2.5	0.115
VQ1000J	60	5.5 @ V <sub>GS</sub> = 10 V	0.8 to 2.5	0.225
VQ1000P		5.5 @ V <sub>GS</sub> = 10 V	0.8 to 2.5	0.225
BS170		5 @ V <sub>GS</sub> = 10 V	0.8 to 3	0.5

#### **FEATURES**

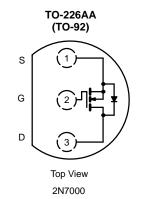
- Low On-Resistance: 2.5 Ω
- Low Threshold: 2.1 V
- Low Input Capacitance: 22 pF
- Fast Switching Speed: 7 ns
- Low Input and Output Leakage

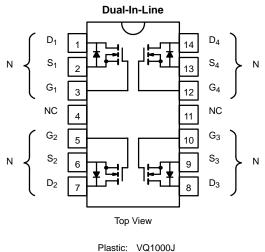
#### BENEFITS

- Low Offset Voltage
- Low-Voltage Operation
- Easily Driven Without Buffer
- High-Speed Circuits
- Low Error Voltage

#### APPLICATIONS

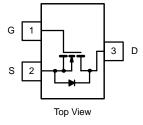
- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays





Plastic: VQ1000J Sidebraze: VQ1000P

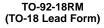


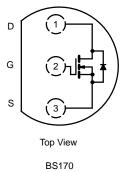


Marking Code: 72*wll* 72 = Part Number Code for 2N7002

w = Week Code

// = Lot Traceability





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#### ABSOLUTE MAXIMUM RATINGS ( $T_{\Delta} = 25^{\circ}C$ UNLESS OTHERWISE NOTED)

					Sin	gle	Total Quad		
Paramete	r	Symbol	2N7000	2N7002	VQ1000J	VQ1000P	VQ1000J/P	BS170	Unit
Drain-Source Voltage		V <sub>DS</sub>	60	60	60	60		60	
Gate-Source Voltage—Non-Repetitive		V <sub>GSM</sub>	±40	± 40	±30			±25	V
Gate-Source Voltage—Continuous		V <sub>GS</sub>	±20	±20	±20	±20		±20	1
Continuous Drain Current $(T_J = 150^{\circ}C)$	$T_A = 25^{\circ}C$		0.2	0.115	0.225	0.225		0.5	
	T <sub>A</sub> = 100°C	۱ <sub>D</sub>	0.13	0.073	0.14	0.14		0.175	Α
Pulsed Drain Currenta	•	I <sub>DM</sub>	0.5	0.8	1	1			1
Davida Diagia atian	$T_A = 25^{\circ}C$		0.4	0.2	1.3	1.3	2	0.83	14/
Power Dissipation	T <sub>A</sub> = 100°C	PD	0.16	0.08	0.52	0.52	0.8		W
Thermal Resistance, Junction-to-Ambient		R <sub>thJA</sub>	312.5	625	96	96	62.5	156	°C/W
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150						°C

Notes a. Pulse width limited by maximum junction temperature. b.  $t_p\,\leq\,50~\mu s.$ 

				2N7000		2N7002		1		
Parameter	Symbol	Test Condit	ions	Typa	Min	Max	Min	Max	Unit	
Static					•				•	
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS}$ = 0 V, I <sub>D</sub> =	10 μA	70	60		60	1		
		$V_{DS} = V_{GS}, I_D = 1 \text{ mA}$		2.1	0.8	3			V	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 0$	0.25 mA	2.0			1	2.5		
Gate-Body Leakage		$V_{DS}$ = 0 V, $V_{GS}$ = ±15 V				±10			nA	
	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$						±100		
Zero Gate Voltage Drain Current		V <sub>DS</sub> = 48 V, V <sub>GS</sub>	s = 0 V			1				
	IDSS		T <sub>C</sub> = 125°C			1000				
		$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$						1	μA	
			T <sub>C</sub> = 125°C					500	1	
		$V_{DS} = 10$ V, $V_{GS} = 4.5$ V		0.35	0.075				A	
On-State Drain Current <sup>b</sup>	D(on)	$V_{DS} = 7.5 V, V_{GS} = 10 V$		1			0.5			
	_	$V_{GS}$ = 4.5 V, I <sub>D</sub> = 0.075 A		4.5		5.3				
		$V_{GS} = 5 \text{ V}, I_D = 0.05 \text{ A}$		3.2				7.5	Ω	
Drain-Source On-Resistance <sup>b</sup>	<sup>r</sup> DS(on)	T <sub>C</sub> = 125°C		5.8				13.5		
		V <sub>GS</sub> = 10 V, I <sub>D</sub> =	0.5 A	2.4		5		7.5		
			T <sub>J</sub> = 125°C	4.4		9		13.5		
Forward Transconductanceb	9 <sub>fs</sub>	$V_{DS} = 10 \text{ V}, I_D = 0.2 \text{ A}$ $V_{DS} = 5 \text{ V}, I_D = 0.05 \text{ A}$			100		80			
Common Source Output Conductance <sup>b</sup>	g <sub>os</sub>			0.5					mS	
Dynamic	· ·				•					
Input Capacitance	C <sub>iss</sub>			22		60		50		
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> f = 1 MHz	s = 0 V	11		25		25	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			2		5	1	5	1	



## 2N7000/2N7002, VQ1000J/P, BS170

## Vishay Siliconix

SPECIFICATIONS—2N7000 AND 2N7002 (T <sub>A</sub> = $25^{\circ}$ C UNLESS OTHERWISE NOTED)											
				2N7000         2N7002           Min         Max         Min         Max							
Parameter	Symbol	Test Conditions	Тура				Мах	Unit			
Switching <sup>d</sup>											
Turn-On Time	t <sub>ON</sub>	$\begin{array}{l} V_{DD} \texttt{=} \texttt{15 V}, R_L\texttt{=} \texttt{25 } \Omega \\ I_D \cong 0.5 \text{ A},  V_{GEN}\texttt{=} \texttt{10 V},  R_G\texttt{=} \texttt{25 } \Omega \end{array}$	7		10						
Turn-Off Time	t <sub>OFF</sub>		7		10			<b>n</b> 0			
Turn-On Time	t <sub>ON</sub>	$V_{DD}$ = 30 V, $R_L$ = 150 $\Omega$	7				20	ns			
Turn-Off Time	t <sub>OFF</sub>	$I_D \cong 0.2 \text{ A}, V_{GEN}$ = 10 V, $R_G$ = 25 $\Omega$	11				20				

				VQ1000J/P		BS170		1
Parameter	Symbol	Test Conditions	Тур <sup>а</sup>	Min	Max	Min	Max	Unit
Static	•							
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 100 \mu\text{A}$		60		60		
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 1 \text{ mA}$	2.1	0.8	2.5	0.8	3	V
		$V_{DS}$ = 0 V, $V_{GS}$ = ±10 V			±100			
Gate-Body Leakage	IGSS	$T_J = 125^{\circ}C$		±50	$\pm 500$		<u> </u>	nA
		$V_{DS}$ = 0 V, $V_{GS}$ = ±15 V				±1	±10	
Zero Gate Voltage Drain Current		$V_{DS} = 25 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$					0.5	μΑ
	IDSS	$V_{DS}$ = 48 V, $V_{GS}$ = 0 V, $T_{J}$ = 125 $^{\circ}$ C		5	500			
		$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			10			1
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	$V_{DS} = 10$ V, $V_{GS} = 10$ V		0.5				А
Drain-Source On-Resistance <sup>b</sup>	rDS(on)	$V_{GS}$ = 5 V, I <sub>D</sub> = 0.2 A	4		7.5			Ω
		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 0.2 \text{ A}$	2.3				5	
		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 0.3 \text{ A}$	2.3		5.5			
		$T_J = 125^{\circ}C$	4.2		7.6			1
Forward Transconductanceb	9fs -	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.2 A				100		
Forward Transconductance		$V_{DS} = 10$ V, $I_{D} = 0.5$ A		100				mS
Common Source Output Conductance <sup>b</sup>	9 <sub>os</sub>	$V_{DS} = 5 V, I_{D} = 0.05 A$	0.5					1
Dynamic								
Input Capacitance	C <sub>iss</sub>		22		60		60	
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =25 V, V <sub>GS</sub> = 0 V f = 1 MHz	11		25			pF
Reverse Transfer Capacitance	C <sub>rss</sub>	1 - 1 101112			5			1
Switching <sup>d</sup>			•	-		•		
Turn-On Time	t <sub>ON</sub>	$V_{DD}$ = 15 V, R <sub>L</sub> = 23 $\Omega$	7		10			T
Turn-Off Time	tOFF	$I_D \approx 0.6 \text{ Å}, V_{GEN} = 10 \text{ V}, \text{ R}_G = 25 \Omega$	7	Ī	10			1
Turn-On Time	t <sub>ON</sub>	$V_{DD}$ = 25 V, R <sub>L</sub> = 125 Ω	7	Ī			10	ns
Turn-Off Time	tOFF	$I_D \cong 0.2 \text{ A}, V_{\text{GEN}} = 10 \text{ V}, R_G = 25 \Omega$			1	1	10	1

 Notes

 a.
 For DESIGN AID ONLY, not subject to production testing.

 b.
 Pulse test: PW ≤ 80 µs duty cycle ≤ 1%.

 c.
 This parameter not registered with JEDEC.

 d.
 Switching time is essentially independent of operating temperature.

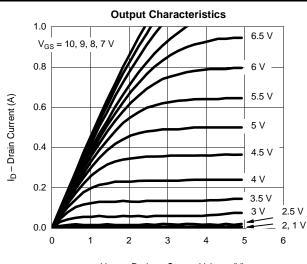
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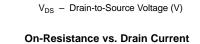
## 2N7000/2N7002, VQ1000J/P, BS170

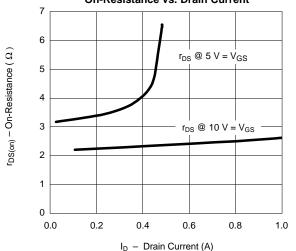
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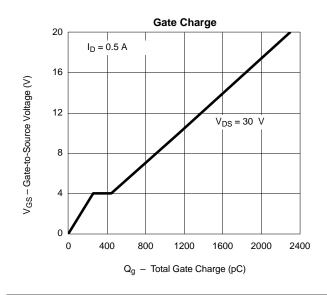


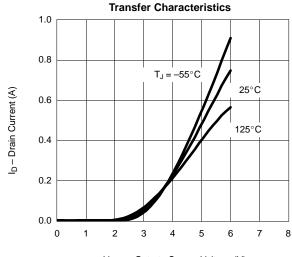
#### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)



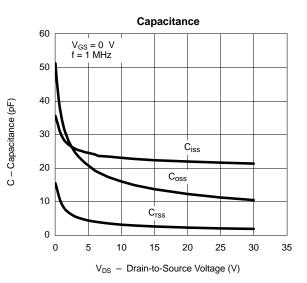


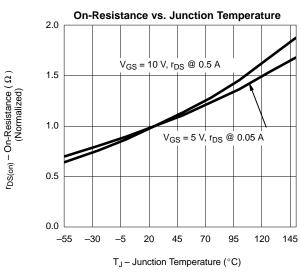






V<sub>GS</sub> - Gate-to-Source Voltage (V)

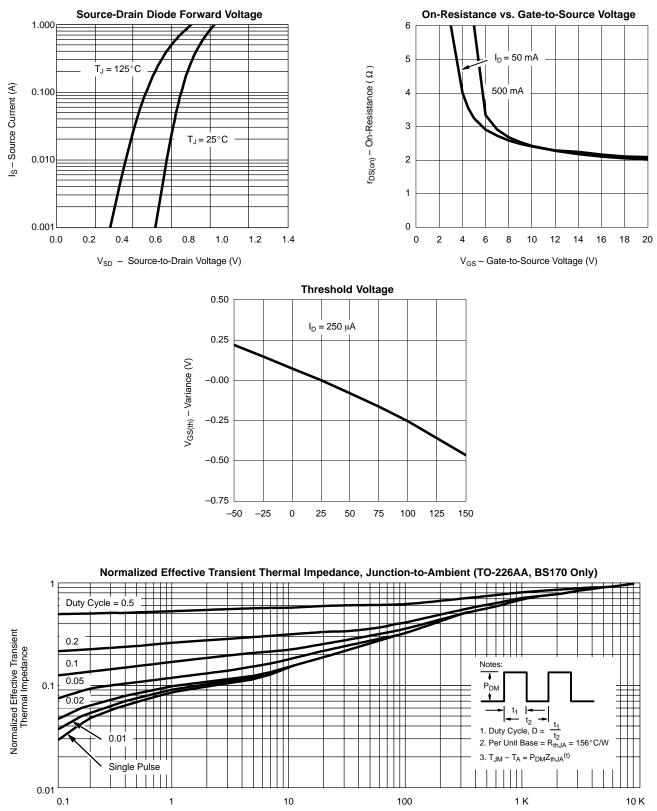






### 2N7000/2N7002, VQ1000J/P, BS170 Vishay Siliconix

#### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)



t<sub>1</sub> – Square Wave Pulse Duration (sec)



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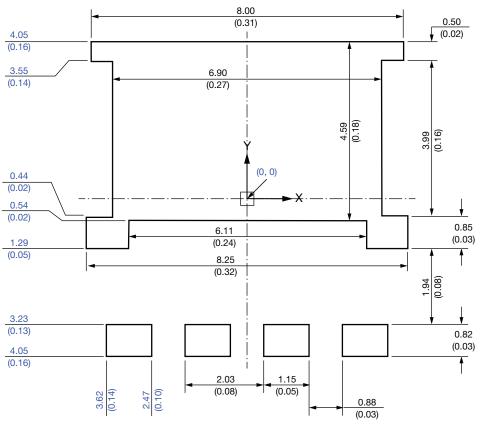
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# **Recommended Minimum PADs for PowerPAK® 8 x 8L Single**



Dimensions in millimeters (inches)

#### Note

• Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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